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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

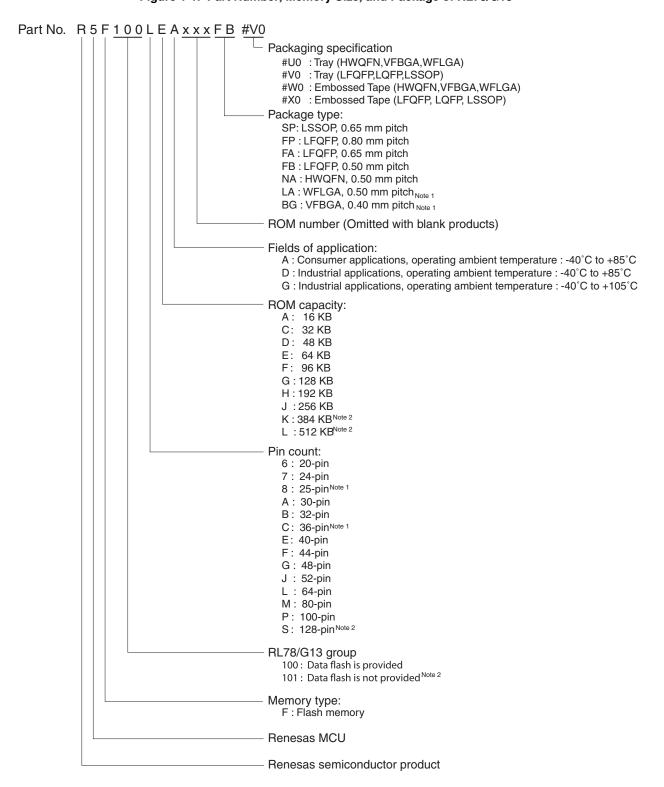
Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	34
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LFQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101gjafb-v0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

1.2 List of Part Numbers

Figure 1-1. Part Number, Memory Size, and Package of RL78/G13



Notes 1. Products only for "A: Consumer applications ($T_A = -40$ to $+85^{\circ}$ C)", and "G: Industrial applications ($T_A = -40$ to $+105^{\circ}$ C)"

2. Products only for "A: Consumer applications ($T_A = -40 \text{ to } +85^{\circ}\text{C}$)", and "D: Industrial applications ($T_A = -40 \text{ to } +85^{\circ}\text{C}$)"

Table 1-1. List of Ordering Part Numbers

(2/12)

				(2/12)
Pin	Package	Data	Fields of	Ordering Part Number
count		flash	Application	
			Note	
25 pins	25-pin plastic	Mounted	Α	R5F1008AALA#U0, R5F1008CALA#U0, R5F1008DALA#U0,
25 pins	· · ·	Mounted	7.	R5F1008EALA#U0
	WFLGA (3 \times 3 mm,			R5F1008AALA#W0, R5F1008CALA#W0, R5F1008DALA#W0,
	0.5 mm pitch)			R5F1008EALA#W0
			G	R5F1008AGLA#U0, R5F1008CGLA#U0, R5F1008DGLA#U0,
				R5F1008EGLA#U0
				R5F1008AGLA#W0, R5F1008CGLA#W0, R5F1008DGLA#W0,
				R5F1008EGLA#W0
		Not	Α	R5F1018AALA#U0, R5F1018CALA#U0, R5F1018DALA#U0,
i		mounted		R5F1018EALA#U0
				R5F1018AALA#W0, R5F1018CALA#W0, R5F1018DALA#W0,
				R5F1018EALA#W0
30 pins	30-pin plastic LSSOP	Mounted	Α	R5F100AAASP#V0, R5F100ACASP#V0, R5F100ADASP#V0,
i	(7.62 mm (300), 0.65			R5F100AEASP#V0, R5F100AFASP#V0, R5F100AGASP#V0
	mm pitch)			R5F100AAASP#X0, R5F100ACASP#X0, R5F100ADASP#X0
	min piton)		_	R5F100AEASP#X0, R5F100AFASP#X0, R5F100AGASP#X0
			D	R5F100AADSP#V0, R5F100ACDSP#V0, R5F100ADDSP#V0,
				R5F100AEDSP#V0, R5F100AFDSP#V0, R5F100AGDSP#V0
				R5F100AADSP#X0, R5F100ACDSP#X0, R5F100ADDSP#X0, R5F100AEDSP#X0, R5F100AFDSP#X0, R5F100AGDSP#X0
			G	R5F100AGSP#V0, R5F100ACGSP#V0,
			G	R5F100ADGSP#V0, R5F100ACGSF#V0,
				R5F100AFGSP#V0, R5F100AGGSP#V0,
				R5F100AAGSP#X0, R5F100ACGSP#X0,
				R5F100ADGSP#X0,R5F100AEGSP#X0,
				R5F100AFGSP#X0, R5F100AGGSP#X0
		Not	Α	R5F101AAASP#V0, R5F101ACASP#V0, R5F101ADASP#V0,
				R5F101AEASP#V0, R5F101AFASP#V0, R5F101AGASP#V0
		mounted		R5F101AAASP#X0, R5F101ACASP#X0, R5F101ADASP#X0,
				R5F101AEASP#X0, R5F101AFASP#X0, R5F101AGASP#X0
			D	R5F101AADSP#V0, R5F101ACDSP#V0, R5F101ADDSP#V0,
				R5F101AEDSP#V0, R5F101AFDSP#V0, R5F101AGDSP#V0
				R5F101AADSP#X0, R5F101ACDSP#X0, R5F101ADDSP#X0,
				R5F101AEDSP#X0, R5F101AFDSP#X0, R5F101AGDSP#X0
32 pins	32-pin plastic	Mounted	Α	R5F100BAANA#U0, R5F100BCANA#U0, R5F100BDANA#U0,
	HWQFN (5×5 mm,			R5F100BEANA#U0, R5F100BFANA#U0, R5F100BGANA#U0
	0.5 mm pitch)			R5F100BAANA#W0, R5F100BCANA#W0, R5F100BDANA#W0,
	0.5 min pitch)			R5F100BEANA#W0, R5F100BFANA#W0, R5F100BGANA#W0
			D	R5F100BADNA#U0, R5F100BCDNA#U0, R5F100BDDNA#U0,
				R5F100BEDNA#U0, R5F100BFDNA#U0, R5F100BGDNA#U0
				R5F100BADNA#W0, R5F100BCDNA#W0, R5F100BDDNA#W0,
				R5F100BEDNA#W0, R5F100BFDNA#W0, R5F100BGDNA#W0
			G	R5F100BAGNA#U0, R5F100BCGNA#U0, R5F100BDGNA#U0,
				R5F100BEGNA#U0, R5F100BFGNA#U0, R5F100BGGNA#U0
				R5F100BAGNA#W0, R5F100BCGNA#W0, R5F100BDGNA#W0,
			_	R5F100BEGNA#W0, R5F100BFGNA#W0, R5F100BGGNA#W0
		Not	Α	R5F101BAANA#U0, R5F101BCANA#U0, R5F101BDANA#U0,
		mounted		R5F101BEANA#U0, R5F101BFANA#U0, R5F101BGANA#U0
				R5F101BAANA#W0, R5F101BCANA#W0, R5F101BDANA#W0,
			D	R5F101BEANA#W0, R5F101BFANA#W0, R5F101BGANA#W0
			٦ ا	R5F101BADNA#U0, R5F101BCDNA#U0, R5F101BDDNA#U0, R5F101BEDNA#U0, R5F101BEDNA#U0
1				R5F101BADNA#W0, R5F101BCDNA#W0, R5F101BDDNA#W0,
				R5F101BEDNA#W0, R5F101BCDNA#W0, R5F101BBDNA#W0,
			1	TOT TO TO EDINA#WO, NOT TO TO FOUNA#WO, NOT TO TO EDINA#WO

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

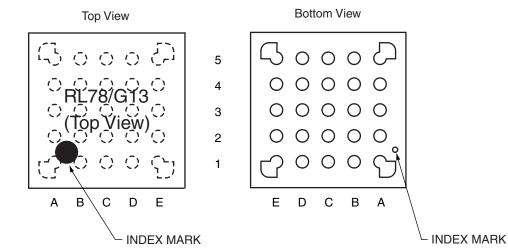
Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



1.3.3 25-pin products

<R>

• 25-pin plastic WFLGA (3 × 3 mm, 0.50 mm pitch)



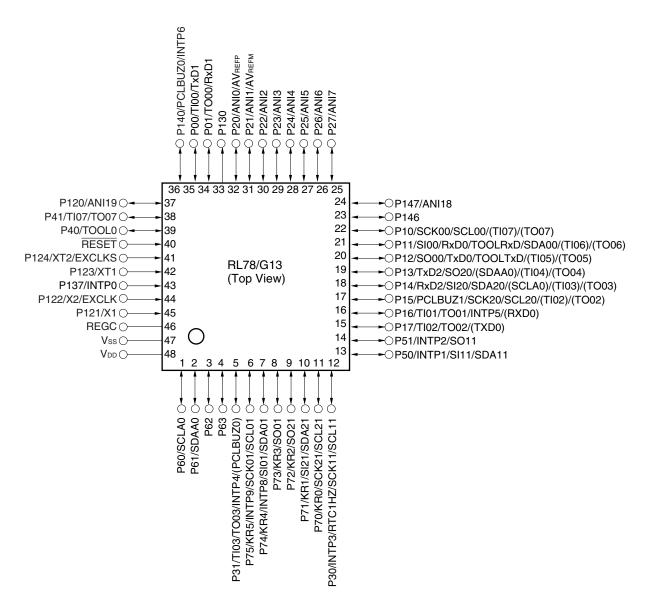
	Α	В	С	D	E	
5	P40/TOOL0	RESET	P01/ANI16/ TO00/RxD1	P22/ANI2	P147/ANI18	5
4	P122/X2/ EXCLK	P137/INTP0	P00/ANI17/ TI00/TxD1	P21/ANI1/ AV _{REFM}	P10/SCK00/ SCL00	4
3	P121/X1	V _{DD}	P20/ANI0/ AV _{REFP}	P12/SO00/ TxD0/ TOOLTxD	P11/SI00/ RxD0/ TOOLRxD/ SDA00	3
2	REGC	Vss	P30/INTP3/ SCK11/SCL11	P17/TI02/ TO02/SO11	P50/INTP1/ SI11/SDA11	2
1	P60/SCLA0	P61/SDAA0	P31/TI03/ TO03/INTP4/ PCLBUZ0	P16/TI01/ TO01/INTP5	P130	1
	A	В	С	D	Е	

Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remark For pin identification, see **1.4 Pin Identification**.

1.3.9 48-pin products

• 48-pin plastic LFQFP (7 x 7 mm, 0.5 mm pitch)

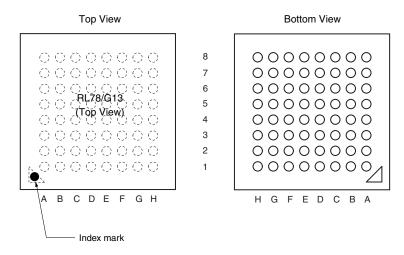


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

• 64-pin plastic VFBGA (4 × 4 mm, 0.4 mm pitch)



Pin No.	Name	Pin No.	Name	Pin No.	Name	Pin No.	Name
A1	P05/TI05/TO05	C1	P51/INTP2/SO11	E1	P13/TxD2/SO20/ (SDAA0)/(TI04)/(TO04)	G1	P146
A2	P30/INTP3/RTC1HZ /SCK11/SCL11	C2	P71/KR1/SI21/SDA21	E2	P14/RxD2/SI20/SDA20 /(SCLA0)/(TI03)/(TO03)	-	P25/ANI5
A3	P70/KR0/SCK21 /SCL21	СЗ	P74/KR4/INTP8/SI01 /SDA01	E3	P15/SCK20/SCL20/ (TI02)/(TO02)	G3	P24/ANI4
A4	P75/KR5/INTP9 /SCK01/SCL01	C4	P52/(INTP10)	E4	P16/TI01/TO01/INTP5 /(SI00)/(RxD0)	G4	P22/ANI2
A5	P77/KR7/INTP11/ (TxD2)	C5	P53/(INTP11)	E5	P03/ANI16/SI10/RxD1 /SDA10	G5	P130
A6	P61/SDAA0	C6	P63	E6	P41/TI07/TO07	G6	P02/ANI17/SO10/TxD1
A7	P60/SCLA0	C7	Vss	E7	RESET	G7	P00/TI00
A8	EV _{DD0}	C8	P121/X1	E8	P137/INTP0	G8	P124/XT2/EXCLKS
B1	P50/INTP1/SI11 /SDA11	D1	P55/(PCLBUZ1)/ (SCK00)	F1	P10/SCK00/SCL00/ (TI07)/(TO07)	H1	P147/ANI18
B2	P72/KR2/SO21	D2	P06/TI06/TO06	F2	P11/SI00/RxD0 /TOOLRxD/SDA00/ (TI06)/(TO06)	H2	P27/ANI7
B3	P73/KR3/SO01	D3	P17/TI02/TO02/ (SO00)/(TxD0)	F3	P12/SO00/TxD0 /TOOLTxD/(INTP5)/ (TI05)/(TO05)	H3	P26/ANI6
B4	P76/KR6/INTP10/ (RxD2)	D4	P54	F4	P21/ANI1/AVREFM	H4	P23/ANI3
B5	P31/TI03/TO03 /INTP4/(PCLBUZ0)	D5	P42/TI04/TO04	F5	P04/SCK10/SCL10	H5	P20/ANI0/AVREFP
B6	P62	D6	P40/TOOL0	F6	P43	H6	P141/PCLBUZ1/INTP7
B7	V _{DD}	D7	REGC	F7	P01/TO00	H7	P140/PCLBUZ0/INTP6
B8	EVsso	D8	P122/X2/EXCLK	F8	P123/XT1	H8	P120/ANI19

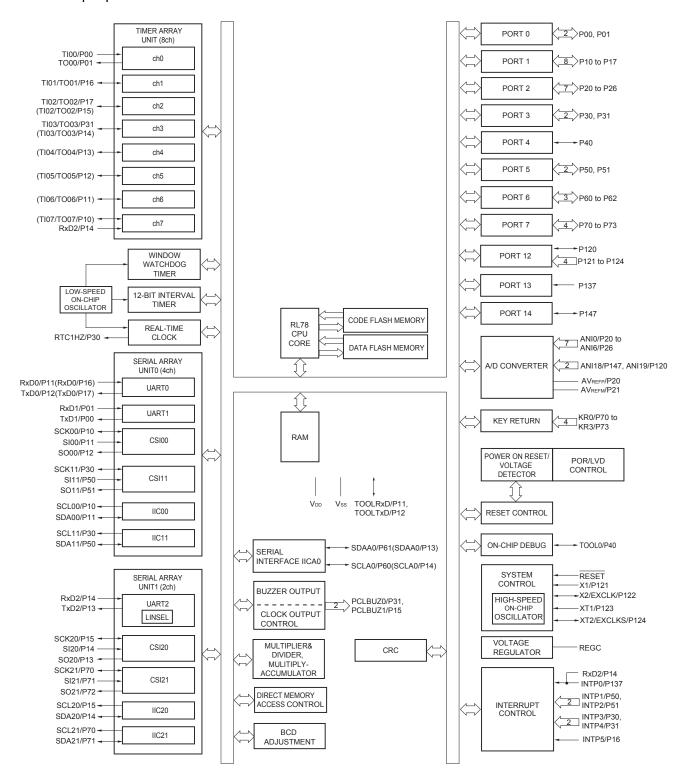
Cautions 1. Make EVsso pin the same potential as Vss pin.

- 2. Make V_{DD} pin the potential that is higher than EV_{DD0} pin.
- 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

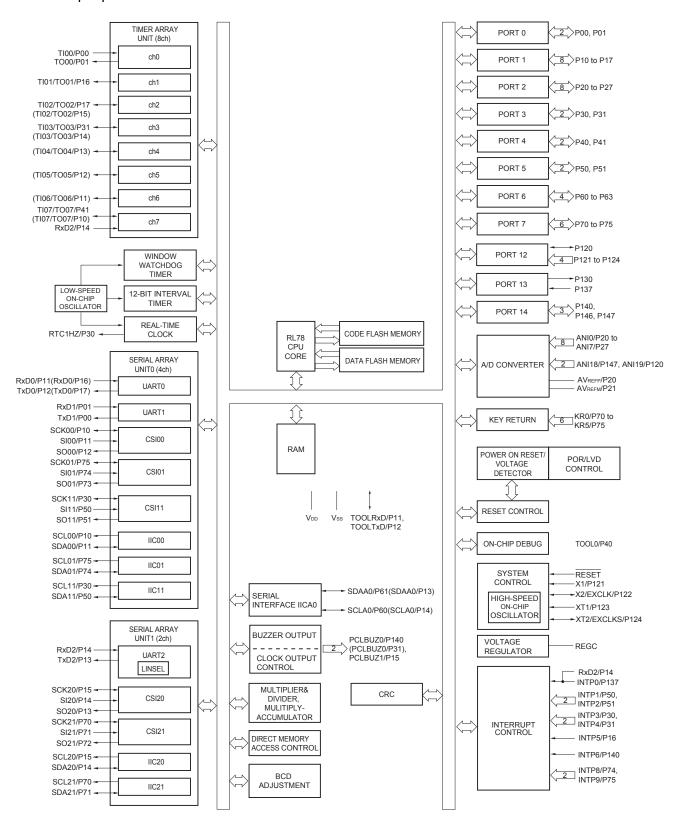
- 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD} and EV_{DD0} pins and connect the Vss and EV_{SS0} pins to separate ground lines.
- **3.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register** (**PIOR**) in the RL78/G13 User's Manual.

1.5.7 40-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

1.5.9 48-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

[80-pin, 100-pin, 128-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

	Itam	90	nin	100	nin	100	(1/Z)			
	Item	80- R5F100Mx	R5F101Mx	R5F100Px	-pin R5F101Px	128 R5F100Sx	R5F101Sx			
Code flash me	emory (KB)		512		o 512		o 512			
Data flash me	- , ,	8	=	8	=	8	=			
RAM (KB)		8 to 3	2 Note 1	8 to 3	2 Note 1	16 to 3	32 Note 1			
Address spac	е	1 MB		1						
Main system clock	High-speed system clock	HS (High-speed HS (High-speed LS (Low-speed	I main) mode: 1 I main) mode: 1 main) mode: 1	external main sys to 20 MHz (V _{DD} = to 16 MHz (V _{DD} = to 8 MHz (V _{DD} = to 4 MHz (V _{DD} =	= 2.7 to 5.5 V), = 2.4 to 5.5 V), 1.8 to 5.5 V),	(EXCLK)				
	High-speed on-chip oscillator	HS (High-speed main) mode: 1 to 32 MHz (V _{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V) XT1 (crystal) oscillation, external subsystem clock input (EXCLKS)								
Subsystem cl	ock	XT1 (crystal) os 32.768 kHz	cillation, externa	l subsystem cloc	k input (EXCLKS	5)				
Low-speed or	n-chip oscillator	15 kHz (TYP.)								
General-purpo	ose register	(8-bit register × 8) × 4 banks								
Minimum insti	ruction execution time	0.03125 μs (Hig	h-speed on-chip	oscillator: fiн = 3	2 MHz operation)				
		0.05 μs (High-speed system clock: f _{MX} = 20 MHz operation)								
		30.5 <i>μ</i> s (Subsys	stem clock: fsub =	= 32.768 kHz ope	ration)					
Instruction se	t	 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 								
I/O port	Total	7	'4	9	92	1	20			
	CMOS I/O	(N-ch O.D. I/O	64 [EV _{DD} withstand e]: 21)	(N-ch O.D. I/O	32 [EV _{DD} withstand je]: 24)	(N-ch O.D. I/O	10 [EV _{DD} withstand e]: 25)			
	CMOS input	!	5		5		5			
	CMOS output		1		1		1			
	N-ch O.D. I/O (withstand voltage: 6 V)		4		4		4			
Timer	16-bit timer	12 cha	nnels	12 cha	annels	16 cha	annels			
	Watchdog timer	1 cha	ınnel	1 cha	annel	1 cha	annel			
	Real-time clock (RTC)	1 cha	nnel	1 cha	annel	1 cha	annel			
	12-bit interval timer (IT)	1 cha	nnel	1 cha	annel	1 cha	annel			
	Timer output	12 channels (PWM outputs:	12 channels 12 channels 16 channels (PWM outputs: 10 Note 2) (PWM outputs: 14 Note 2) (PWM outputs: 14 Note 2)							
	RTC output	1 channel • 1 Hz (subsyst	em clock: fsub =	32.768 kHz)						

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xJ, R5F101xJ (x = M, P): Start address FAF00H R5F100xL, R5F101xL (x = M, P, S): Start address F7F00H

For the RAM areas used by the flash library, see Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944).

Absolute Maximum Ratings (TA = 25°C) (2/2)

Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-40	mA
		Total of all pins -170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	-70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	-100	mA
	І ОН2	Per pin	P20 to P27, P150 to P156	-0.5	mA
		Total of all pins		-2	mA
Output current, low	lo _{L1}	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	40	mA
		Total of all pins 170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	100	mA
	lo _{L2}	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins		5	mA
Operating ambient	TA	In normal operati	on mode	-40 to +85	°C
temperature		In flash memory	programming mode		
Storage temperature	Tstg			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

- Notes 1. Total current flowing into VDD, EVDDO, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO, and EVDD1, or Vss, EVSSO, and EVSS1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V \leq VDD \leq 5.5 V@1 MHz to 32 MHz

 $2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 16 MHz

LS (low-speed main) mode: $1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}@1 \text{ MHz}$ to 8 MHz LV (low-voltage main) mode: $1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}@1 \text{ MHz}$ to 4 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - **3.** fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

Note The following conditions are required for low voltage interface when EVDDO < VDD

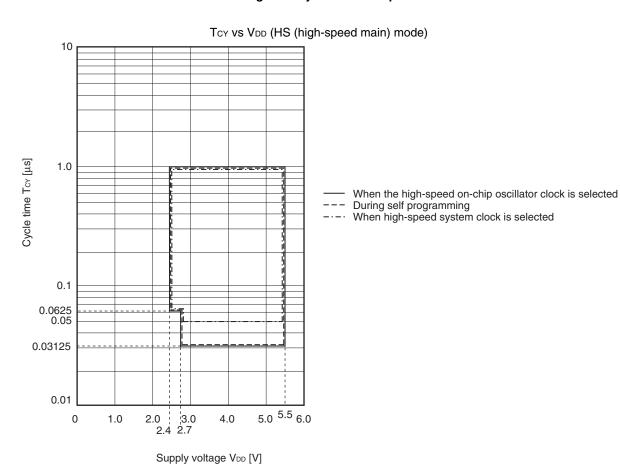
 $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V} : \text{MIN. } 125 \text{ ns}$ $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V} : \text{MIN. } 250 \text{ ns}$

Remark fmck: Timer array unit operation clock frequency

(Operation clock to be set by the CKSmn0, CKSmn1 bits of timer mode register mn (TMRmn).

m: Unit number (m = 0, 1), n: Channel number (n = 0 to 7))

Minimum Instruction Execution Time during Main System Clock Operation



(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \leq \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	C	Conditions	HS (high main)	•	LS (low main)	•	LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tксү1 ≥ 4/fс∟к	$2.7~V \leq EV_{DD0} \leq 5.5$ V	125		500		1000		ns
			$2.4~V \leq EV_{DD0} \leq 5.5$ V	250		500		1000		ns
			$1.8~V \le EV_{DD0} \le 5.5$ V	500		500		1000		ns
			$1.7~V \le EV_{DD0} \le 5.5$ V	1000		1000		1000		ns
			$1.6~V \le EV_{DD0} \le 5.5$ V	_		1000		1000		ns
SCKp high-/low-level width	tkhi, tkli	4.0 V ≤ EV _{DD0} ≤ 5.5 V		tксү1/2 – 12		tксу1/2 — 50		tксү1/2 – 50		ns
		$2.7~\text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5~\text{V}$		tксү1/2 – 18		tксу1/2 — 50		tксү1/2 – 50		ns
		$2.4~V \le EV_{DD0} \le 5.5~V$		tксү1/2 – 38		tксу1/2 — 50		tксү1/2 — 50		ns
		$1.8~V \leq EV_{DD0} \leq 5.5~V$		tксү1/2 — 50		tксү1/2 — 50		tксү1/2 – 50		ns
		1.7 V ≤ EV _D	00 ≤ 5.5 V	tксу1/2 — 100		tксу1/2 — 100		tксу1/2 — 100		ns
		1.6 V ≤ EVD	₀₀ ≤ 5.5 V	_		tксу1/2 — 100		tксу1/2 — 100		ns
SIp setup time	tsıĸı	4.0 V ≤ EV _{DI}	00 ≤ 5.5 V	44		110		110		ns
(to SCKp↑)		2.7 V ≤ EV _{DI}	00 ≤ 5.5 V	44		110		110		ns
		2.4 V ≤ EV _{DI}	00 ≤ 5.5 V	75		110		110		ns
		1.8 V ≤ EV _{DI}	oo ≤ 5.5 V	110		110		110		ns
		1.7 V ≤ EV _{DI}	oo ≤ 5.5 V	220		220		220		ns
		1.6 V ≤ EV _{DI}	00 ≤ 5.5 V	_		220		220		ns
SIp hold time	tksi1	1.7 V ≤ EV _{DI}	00 ≤ 5.5 V	19		19		19		ns
(from SCKp↑) Note 2		1.6 V ≤ EV _{DI}	00 ≤ 5.5 V	_		19		19		ns
Delay time from SCKp↓ to SOp	tkso1	$1.7 \text{ V} \le \text{EV}_{DI}$ $C = 30 \text{ pF}^{\text{Note}}$			25		25		25	ns
output Note 3		$1.6 \text{ V} \leq \text{EV}_{DI}$ $C = 30 \text{ pF}^{\text{Note}}$			_		25		25	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

- 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),

g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)

2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13))

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (1/2)

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Condit	ions	, •	h-speed Mode	LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy2	$4.0~V \leq EV_{DD0} \leq 5.5$	20 MHz < fмск	8/fмск		_		_		ns
Note 5		V	fмcκ ≤ 20 MHz	6/ƒмск		6/fмск		6/fмск		ns
		$2.7~V \le EV_{DD0} \le 5.5$ V	16 MHz < fмск	8/fмск		_		_		ns
			fмск ≤ 16 MHz	6/ƒмск		6/fмск		6/fмск		ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V		6/fмск and 500		6/fмск and 500		6/fмск and 500		ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		6/fмск and 750		6/fмск and 750		6/fмск and 750		ns
	$1.7~V \le EV_{DD0} \le 5.5~V$			6/fмск and 1500		6/fмск and 1500		6/fмск and 1500		ns
		1.6 V ≤ EV _{DD0} ≤ 5.5	V	_		6/fмск and 1500		6/fмск and 1500		ns
SCKp high-/low- level width	tкн2, tкL2	$4.0~\text{V} \le \text{EV}_\text{DD0} \le 5.5~\text{V}$		tксү2/2 – 7		tксу2/2 - 7		tксү2/2 - 7		ns
		2.7 V ≤ EV _{DD0} ≤ 5.5 V		tксү2/2 – 8		tксу2/2 - 8		tксу2/2 - 8		ns
		$1.8~V \leq EV_{DD0} \leq 5.5~V$		tксу2/2 — 18		tксу2/2 - 18		tксу2/2 - 18		ns
		1.7 V ≤ EV _{DD0} ≤ 5.5 V	$1.7~V \leq EV_{DD0} \leq 5.5~V$			tксу2/2 - 66		tксү2/2 - 66		ns
		$1.6~V \leq EV_{DD0} \leq 5.5~V$		_		tксу2/2 - 66		tксу2/2 - 66		ns

(Notes, Caution, and Remarks are listed on the next page.)

3.2 Oscillator Characteristics

3.2.1 X1, XT1 oscillator characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation	Ceramic resonator/	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	1.0		20.0	MHz
frequency (fx) ^{Note}	crystal resonator	$2.4~V \leq V_{DD} < 2.7~V$	1.0		16.0	MHz
XT1 clock oscillation frequency (fx) ^{Note}	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, refer to 5.4 System Clock Oscillator.

3.2.2 On-chip oscillator characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

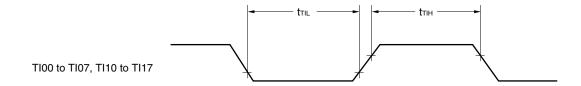
Oscillators	Parameters		Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	fін			1		32	MHz
High-speed on-chip oscillator		–20 to +85 °C	$2.4~V \leq V_{DD} \leq 5.5~V$	-1.0		+1.0	%
clock frequency accuracy		–40 to −20 °C	$2.4~V \leq V_{DD} \leq 5.5~V$	-1.5		+1.5	%
		+85 to +105 °C	$2.4~V \leq V_{DD} \leq 5.5~V$	-2.0		+2.0	%
Low-speed on-chip oscillator clock frequency	fı∟				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

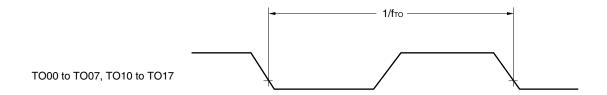
- **Notes 1.** High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H/010C2H) and bits 0 to 2 of HOCODIV register.
 - 2. This indicates the oscillator characteristics only. Refer to AC Characteristics for instruction execution time.

- **6.** Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter is in operation.
- 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
- 8. Current flowing only during data flash rewrite.
- **9.** Current flowing only during self programming.
- 10. For shift time to the SNOOZE mode, see 18.3.3 SNOOZE mode in the RL78/G13 User's Manual.
- Remarks 1. fil: Low-speed on-chip oscillator clock frequency
 - 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 3. fclk: CPU/peripheral hardware clock frequency
 - **4.** Temperature condition of the TYP. value is $T_A = 25^{\circ}C$

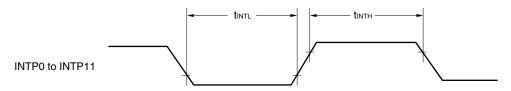


TI/TO Timing

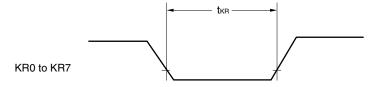




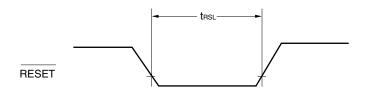
Interrupt Request Input Timing



Key Interrupt Input Timing



RESET Input Timing



(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Condit	ions	HS (high-spee	ed main) Mode	Unit
					MIN.	MAX.	
Transfer rate		Transmission	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$			Note 1	bps
			V , $2.7 \text{ V} \le V_b \le 4.0 \text{ V}$ $2.7 \text{ V} \le EV_{DD0} < 4.0 \text{ V}$	Theoretical value of the maximum transfer rate $C_b = 50 \ pF, \ R_b = 1.4 \ k\Omega, \ V_b = 2.7 \ V$		2.6 Note 2	Mbps
			2.7 V ≤ EV _{DD0} < 4.0			Note 3	bps
	$\begin{array}{c} V,\\ V,\\ 2.3\ V \leq V_b \leq 2.7\ V \end{array}$		Theoretical value of the maximum transfer rate $C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega, \ V_b = 2.3 \ V$		1.2 Note 4	Mbps	
			2.4 V ≤ EV _{DD0} < 3.3			Note 5	bps
	$V,$ $1.6~V \leq V_b \leq 2.0~V$	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 V$		0.43 Note 6	Mbps		

Notes 1. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq EV_{DD0} \leq 5.5 V and 2.7 V \leq V_b \leq 4.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.2}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- 2. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- 3. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq EV_{DDO} < 4.0 V and 2.4 V \leq V_b \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.0}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.



4.9 48-pin Products

R5F100GAAFB, R5F100GCAFB, R5F100GDAFB, R5F100GEAFB, R5F100GFAFB, R5F100GAFB, R5F100GHAFB, R5F100GJAFB, R5F100GKAFB, R5F100GLAFB

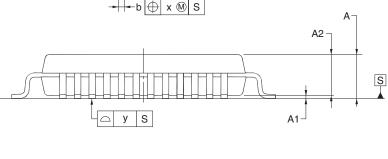
R5F101GAAFB, R5F101GCAFB, R5F101GDAFB, R5F101GEAFB, R5F101GFAFB, R5F101GHAFB, R5F101GJAFB, R5F101GKAFB, R5F101GLAFB

R5F100GADFB, R5F100GCDFB, R5F100GDDFB, R5F100GEDFB, R5F100GFDFB, R5F100GHDFB, R5F100GHDFB, R5F100GHDFB, R5F100GHDFB, R5F100GHDFB

R5F101GADFB, R5F101GCDFB, R5F101GDDFB, R5F101GEDFB, R5F101GFDFB, R5F101GHDFB, R5F101GJDFB, R5F101GKDFB, R5F101GKDFB, R5F101GKDFB, R5F101GKDFB

R5F100GAGFB, R5F100GCGFB, R5F100GDGFB, R5F100GEGFB, R5F100GFGFB, R5F100GHGFB, R5F10

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP48-7x7-0.50	PLQP0048KF-A	P48GA-50-8EU-1	0.16	
HD————————————————————————————————————	25 24	E HE	detail of le	CL
48	13			(UNIT:mn
. 1	12.	↓	D	DIMENSIONS
		<u></u>		7.00±0.20 7.00±0.20
		<u> </u>	HD	9.00±0.20
	. 4 4 0 0	<u>T</u> _	HE	9.00±0.20 9.00±0.20
-ZD	→ e		A	1.60 MAX.
			A1	0.10±0.05
	x (M) S	Δ		1.40±0.05
		A		0.25
		A2 ¬	b	0.22±0.05



Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

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0.145 ^{+0.055} -0.045 0.50

0.60±0.15

1.00±0.20 3°+5° 0.50 0.08 0.08

0.75

0.75

Lp

ZD

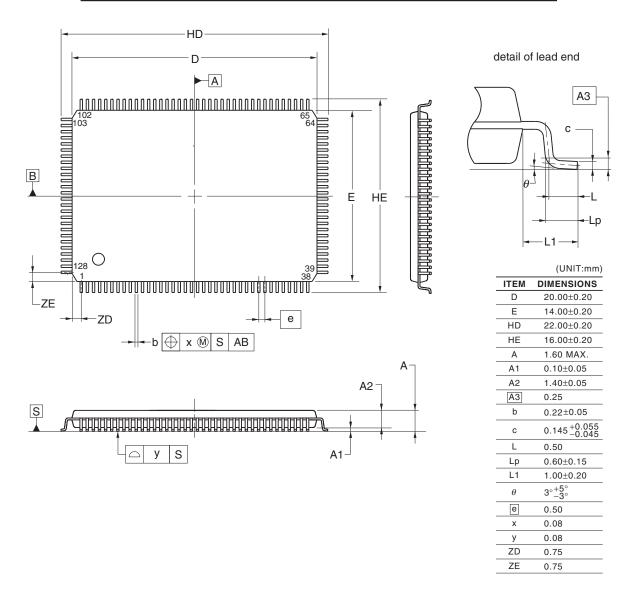
ZE



4.14 128-pin Products

R5F100SHAFB, R5F100SJAFB, R5F100SKAFB, R5F100SLAFB R5F101SHAFB, R5F101SJAFB, R5F101SKAFB, R5F101SLAFB R5F100SHDFB, R5F100SJDFB, R5F100SKDFB, R5F100SLDFB R5F101SHDFB, R5F101SJDFB, R5F101SKDFB, R5F101SLDFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP128-14x20-0.50	PLQP0128KD-A	P128GF-50-GBP-1	0.92



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			Description		
Rev.	Date	Page	Summary		
3.00	Aug 02, 2013	118	Modification of table in 2.6.2 Temperature sensor/internal reference voltage characteristics		
		118	Modification of table and note in 2.6.3 POR circuit characteristics		
	119	Modification of table in 2.6.4 LVD circuit characteristics			
	120	Modification of table of LVD Detection Voltage of Interrupt & Reset Mode			
	120	Renamed to 2.6.5 Power supply voltage rising slope characteristics			
		122	Modification of table, figure, and remark in 2.10 Timing Specs for Switch Flash Memory Programming Modes		
	123	Modification of caution 1 and description			
		124	Modification of table and remark 3 in Absolute Maximum Ratings (T _A = 25°C)		
		126	Modification of table, note, caution, and remark in 3.2.1 X1, XT1 oscillator characteristics		
	126	Modification of table in 3.2.2 On-chip oscillator characteristics			
		127	Modification of note 3 in 3.3.1 Pin characteristics (1/5)		
		128	Modification of note 3 in 3.3.1 Pin characteristics (2/5)		
	133	Modification of notes 1 and 4 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (1/2)			
		135	Modification of notes 1, 5, and 6 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (2/2)		
		137	Modification of notes 1 and 4 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (1/2)		
	139	Modification of notes 1, 5, and 6 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (2/2)			
		140	Modification of (3) Peripheral Functions (Common to all products)		
	142	Modification of table in 3.4 AC Characteristics			
		143	Addition of Minimum Instruction Execution Time during Main System Clock Operation		
		143	Modification of figure of AC Timing Test Points		
		143	Modification of figure of External System Clock Timing		
		145	Modification of figure of AC Timing Test Points		
		145	Modification of description, note 1, and caution in (1) During communication at same potential (UART mode)		
		146	Modification of description in (2) During communication at same potential (CSI mode)		
		147	Modification of description in (3) During communication at same potential (CSI mode)		
		149	Modification of table, note 1, and caution in (4) During communication at same potential (simplified I ² C mode)		
		151	Modification of table, note 1, and caution in (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)		
		152 to 154	Modification of table, notes 2 to 6, caution, and remarks 1 to 4 in (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)		
		155	Modification of table in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/3)		
		156	Modification of table and caution in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/3)		
		157, 158	Modification of table, caution, and remarks 3 and 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)		
		160, 161	Modification of table and caution in (7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode)		